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Electronic Supplementary Information

for

Tailoring electronic properties of multilayer phosphorene by siliconization

Oleksandr I. Malyi¹, Kostiantyn V. Sopiha², Ihor Radchenko², Ping Wu² and Clas Persson¹

1 - Centre for Materials Science and Nanotechnology, Department of Physics, University of

Oslo, P. O. Box 1048 Blindern, NO-0316 Oslo, Norway

2 - Engineering Product Development, Singapore University of Technology and Design, 8

Somapah Road, 487372 Singapore, Singapore

email: <u>oleksandrmalyi@gmail.com</u> (O.I.M)



Figure S1 HSE energy gaps of bilayer 2d-SiP (left) and 2d-SiP₂ (right). The results are given for structures from different functionals.



Figure S2 Local densities of states (LDOS) projected on the outermost (left column) and central (right column) layers of 2d-P with different thicknesses computed using optB88-vdW functional. All energies are given with respect to the vacuum level.



Figure S3 Integrated layer-resolved local densities of states (LDOS) for 5-layer 2d-P, 2d- $SiP(Cmc2_1)$, and 2d- $SiP_2(Pnma)$ computed using HSE. The k-point grids adopted in HSE calculations are scarcer compared to those in optB88-vdW (see Table S1). The integrated LDOS are calculated by integrating the LDOS over energy and given with respect to that for VBM (or CBM).



Figure S4 Illustration of the layer indexing for 5-layer 2d-P, $2d-SiP(Cmc2_1)$, and $2d-SiP_2(Pnma)$.

	HSE	Relaxation	Correction	LDOS	LDOS	BOMD
				(optB88-vdW)	(HSE)	
2d-P	7×7×1	14×14×1	-	48×48×1	$7 \times 7 \times 1$	-
2d-SiP	7×7×1	18×8×1	18×8×1	48×16×1	$7 \times 7 \times 1$	$1 \times 1 \times 1$
2d-SiP ₂	9×4×1	18×8×1	18×8×1	48×16×1	9×4×1	$1 \times 1 \times 1$

Table S1 The k-point grids used in different calculations. The $6 \times 2 \times 1$ supercells (144 atoms)are used for BOMD simulations and the conventional standard cells are analyzed otherwise.

Table S2 Summary of electronic properties of bulk P, SiP, and SiP2. The results are given foroptB88-vdW relaxed structures

System	HSE band gap (eV)
Р	0.38
SiP(<i>Cmc</i> 2 ₁)	1.88
SiP(C2/m)	1.59
SiP ₂ (Pnma)	2.00
SiP ₂ (<i>Pbam</i>)	1.83

Functional	Number of	Lattice	Lattice	HSE band gap	Interaction energy
	layers	constant a (A)	constant b (A)	(eV)	(meV/atom)
DFT-D2	1	4.57	3.31	1.56	0
DFT-D2	2	4.51	3.31	1.03	-39
DFT-D2	3	4.48	3.32	0.77	-53
DFT-D2	4	4.47	3.32	0.64	-59
DFT-D2	5	4.46	3.32	0.54	-64
optB86b-vdW	1	4.51	3.30	1.46	0
optB86b-vdW	2	4.43	3.32	0.88	-59
optB86b-vdW	3	4.41	3.32	0.60	-79
optB86b-vdW	4	4.40	3.32	0.47	-90
optB86b-vdW	5	4.37	3.32	0.33	-96
optB88-vdW	1	4.58	3.32	1.52	0
optB88-vdW	2	4.53	3.33	1.04	-55
optB88-vdW	3	4.51	3.33	0.80	-73
optB88-vdW	4	4.49	3.34	0.68	-83
optB88-vdW	5	4.49	3.34	0.61	-89
optPBE-vdW	1	4.63	3.32	1.56	0
optPBE-vdW	2	4.58	3.33	1.13	-47
optPBE-vdW	3	4.57	3.33	0.94	-63
optPBE-vdW	4	4.56	3.33	0.83	-71
optPBE-vdW	5	4.56	3.34	0.77	-76
PBE	1	4.63	3.30	1.59	0
PBE	2	4.59	3.30	1.22	-5
PBE	3	4.58	3.30	1.04	-7
PBE	4	4.57	3.30	0.94	-7
PBE	5	4.56	3.30	0.87	-8

 Table S3 Summary on the computed properties of 2d-P systems

Functional	Number of layers	Lattice constant a (Å)	Lattice constant b (Å)	HSE band gap (eV)	Band gap correction (eV)	Corrected HSE band gap (eV)	Interaction energy (meV/atom)
DFT-D2	1	3.52	10.37	2.68	0.01	2.66	0
DFT-D2	2	3.52	10.39	2.22	0.03	2.19	-20
DFT-D2	3	3.52	10.40	2.02	0.03	1.99	-28
DFT-D2	4	3.52	10.40	1.94	0.03	1.91	-31
DFT-D2	5	3.52	10.41	1.89	0.03	1.86	-34
optB86b-vdW	1	3.52	10.37	2.68	0.03	2.65	0
optB86b-vdW	2	3.52	10.40	2.29	0.05	2.24	-32
optB86b-vdW	3	3.52	10.42	2.10	0.06	2.04	-44
optB86b-vdW	4	3.52	10.42	2.02	0.07	1.95	-49
optB86b-vdW	5	3.52	10.42	1.98	0.07	1.90	-53
optB88-vdW	1	3.54	10.47	2.68	0.01	2.67	0
optB88-vdW	2	3.55	10.50	2.29	0.06	2.23	-32
optB88-vdW	3	3.55	10.51	2.12	0.07	2.04	-43
optB88-vdW	4	3.55	10.51	2.04	0.08	1.96	-49
optB88-vdW	5	3.55	10.52	2.00	0.08	1.92	-52
optPBE-vdW	1	3.54	10.47	2.67	0.01	2.66	0
optPBE-vdW	2	3.55	10.49	2.37	0.04	2.33	-28
optPBE-vdW	3	3.55	10.50	2.22	0.06	2.16	-38
optPBE-vdW	4	3.55	10.50	2.15	0.07	2.09	-43
optPBE-vdW	5	3.55	10.51	2.12	0.07	2.05	-46
PBE	1	3.53	10.43	2.67	0.01	2.66	0
PBE	2	3.53	10.43	2.60	0.02	2.58	-1
PBE	3	3.53	10.43	2.57	0.02	2.54	-1
PBE	4	3.53	10.43	2.55	0.03	2.53	-1
PBE	5	3.53	10.43	2.54	0.03	2.52	-2

Table S4 Summary on the computed properties of 2d-SiP(*Cmc*2₁) systems

Functional	Number of layers	Lattice constant a (Å)	Lattice constant b (Å)	HSE band gap (eV)	Band gap correction (eV)	Corrected HSE band gap (eV)	Interaction energy (meV/atom)
DFT-D2	1	3.52	10.37	2.68	0.02	2.66	0
DFT-D2	2	3.52	10.39	2.03	0.03	2.01	-20
DFT-D2	3	3.53	10.40	1.80	0.04	1.76	-27
DFT-D2	4	3.53	10.41	1.70	0.05	1.65	-31
DFT-D2	5	3.53	10.41	1.65	0.06	1.60	-33
optB86b-vdW	1	3.52	10.37	2.68	0.03	2.65	0
optB86b-vdW	2	3.53	10.41	2.09	0.06	2.03	-32
optB86b-vdW	3	3.53	10.42	1.86	0.09	1.77	-44
optB86b-vdW	4	3.53	10.43	1.76	0.10	1.67	-49
optB86b-vdW	5	3.53	10.43	1.71	0.10	1.62	-53
optB88-vdW	1	3.54	10.46	2.68	0.01	2.67	0
optB88-vdW	2	3.55	10.50	2.11	0.09	2.02	-32
optB88-vdW	3	3.55	10.51	1.90	0.10	1.80	-43
optB88-vdW	4	3.56	10.52	1.81	0.09	1.71	-49
optB88-vdW	5	3.56	10.52	1.76	0.09	1.67	-52
optPBE-vdW	1	3.54	10.47	2.67	0.01	2.66	0
optPBE-vdW	2	3.55	10.49	2.23	0.07	2.16	-28
optPBE-vdW	3	3.55	10.50	2.05	0.09	1.96	-38
optPBE-vdW	4	3.55	10.51	1.98	0.10	1.87	-43
optPBE-vdW	5	3.55	10.51	1.94	0.11	1.83	-46
PBE	1	3.53	10.43	2.67	0.01	2.66	0
PBE	2	3.53	10.43	2.55	0.02	2.53	-1
PBE	3	3.53	10.43	2.49	0.02	2.47	-1
PBE	4	3.53	10.43	2.46	0.02	2.44	-1
PBE	5	3.53	10.43	2.44	0.02	2.42	-1

 Table S5 Summary on the computed properties of 2d-SiP(C2/m) systems

Functional	Number of layers	Lattice constant a (Å)	Lattice constant b (Å)	HSE band gap (eV)	Band gap correction (eV)	Corrected HSE band gap (eV)	Interaction energy (meV/atom)
DFT-D2	1	3.45	10.02	2.22	0.01	2.21	0
DFT-D2	2	3.45	10.04	2.01	0.00	2.01	-23
DFT-D2	3	3.45	10.04	1.97	0.00	1.97	-31
DFT-D2	4	3.44	10.04	1.93	0.00	1.93	-36
DFT-D2	5	3.44	10.04	1.92	0.00	1.92	-38
optB86b-vdW	1	3.45	9.95	2.22	0.01	2.20	0
optB86b-vdW	2	3.45	10.02	2.03	0.00	2.03	-36
optB86b-vdW	3	3.45	10.03	1.97	0.00	1.97	-49
optB86b-vdW	4	3.45	10.04	1.94	0.00	1.94	-55
optB86b-vdW	5	3.45	10.05	1.93	0.00	1.93	-59
optB88-vdW	1	3.47	10.10	2.26	0.01	2.24	0
optB88-vdW	2	3.47	10.16	2.09	0.01	2.08	-35
optB88-vdW	3	3.47	10.17	2.07	0.01	2.06	-48
optB88-vdW	4	3.47	10.18	2.04	0.00	2.04	-54
optB88-vdW	5	3.47	10.18	2.03	0.00	2.03	-58
optPBE-vdW	1	3.47	10.20	2.31	0.02	2.29	0
optPBE-vdW	2	3.47	10.25	2.16	0.01	2.15	-31
optPBE-vdW	3	3.47	10.27	2.15	0.02	2.13	-42
optPBE-vdW	4	3.47	10.27	2.13	0.01	2.12	-48
optPBE-vdW	5	3.47	10.27	2.13	0.01	2.12	-51
PBE	1	3.45	10.28	2.36	0.03	2.33	0
PBE	2	3.45	10.31	2.29	0.02	2.26	-1
PBE	3	3.45	10.31	2.28	0.04	2.24	-2
PBE	4	3.45	10.31	2.26	0.03	2.23	-2
PBE	5	3.45	10.31	2.26	0.04	2.22	-2

Table S6 Summary on the computed properties of 2d-SiP₂(*Pnma*) systems

Functional	Number of layers	Lattice constant a (Å)	Lattice constant b (Å)	HSE band gap (eV)	Band gap correction (eV)	Corrected HSE band gap (eV)	Interaction energy (meV/atom)
DFT-D2	1	3.45	10.01	2.22	0.01	2.21	0
DFT-D2	2	3.45	9.94	1.96	0.00	1.96	-21
DFT-D2	3	3.45	9.92	1.94	0.02	1.93	-29
DFT-D2	4	3.45	9.86	1.85	0.00	1.85	-33
DFT-D2	5	3.45	9.84	1.81	0.00	1.81	-35
optB86b-vdW	1	3.45	9.94	2.21	0.01	2.20	0
optB86b-vdW	2	3.45	9.85	1.96	0.01	1.95	-35
optB86b-vdW	3	3.45	9.81	1.87	0.01	1.86	-47
optB86b-vdW	4	3.45	9.79	1.80	0.00	1.80	-54
optB86b-vdW	5	3.45	9.78	1.77	0.00	1.77	-57
optB88-vdW	1	3.47	10.10	2.25	0.01	2.24	0
optB88-vdW	2	3.47	10.01	2.00	0.00	2.00	-34
optB88-vdW	3	3.48	9.99	1.98	0.01	1.97	-46
optB88-vdW	4	3.48	9.97	1.93	0.01	1.92	-52
optB88-vdW	5	3.48	9.96	1.90	0.01	1.90	-55
optPBE-vdW	1	3.47	10.20	2.31	0.02	2.29	0
optPBE-vdW	2	3.47	10.16	2.11	0.01	2.11	-30
optPBE-vdW	3	3.47	10.15	2.10	0.04	2.06	-40
optPBE-vdW	4	3.48	10.14	2.06	0.03	2.03	-46
optPBE-vdW	5	3.48	10.14	2.06	0.03	2.03	-49
PBE	1	3.45	10.29	2.37	0.03	2.34	0
PBE	2	3.45	10.28	2.27	0.03	2.24	-1
PBE	3	3.45	10.29	2.26	0.05	2.22	-2
PBE	4	3.45	10.27	2.23	0.05	2.19	-2
PBE	5	3.45	10.27	2.22	0.05	2.18	-2

Table S7 Summary on the computed properties of SiP₂(*Pbam*) systems

System	1 layer	2 layers	3 layers	4 layers	5 layers
2d-P	Pman	Pbma	Pman	Pbma	Pman
$2d-SiP(Cmc2_1)$	<i>C</i> 2/ <i>m</i> 11	<i>Cm</i> 11	<i>Cm</i> 11	<i>Cm</i> 11	<i>Cm</i> 11
2d-SiP(C2/m)	<i>C</i> 2/ <i>m</i> 11				
2d-SiP ₂ (<i>Pnma</i>)	$Pm2_1b$	$P2_1/m11$	$Pm2_1b$	$P2_1/m11$	$Pm2_1b$
2d-SiP ₂ (<i>Pbam</i>)	$Pm2_1b$	<i>P2/m</i> 11	$Pm2_1b$	<i>P2/m</i> 11	$Pm2_1b$

Table S8 Layer groups of the considered 2d materials